

To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

1. Renesas Technology Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.

Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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2SD467

Silicon NPN Epitaxial

RENESAS

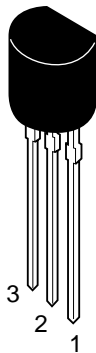
ADE-208-1134 (Z)
1st. Edition
Mar. 2001

Application

- Low frequency power amplifier
- Complementary pair with 2SB561

Outline

TO-92 (1)



1. Emitter
2. Collector
3. Base

Absolute Maximum Ratings (Ta = 25°C)

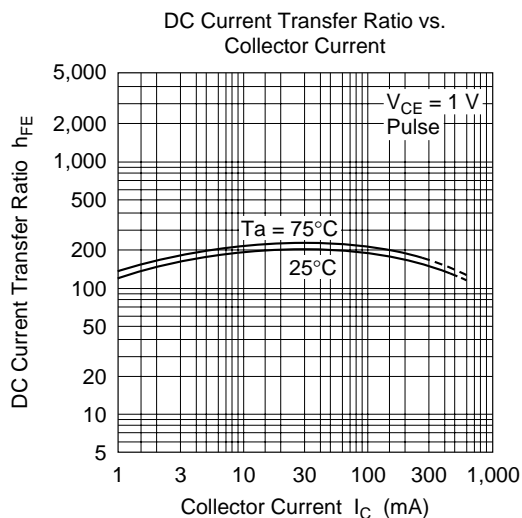
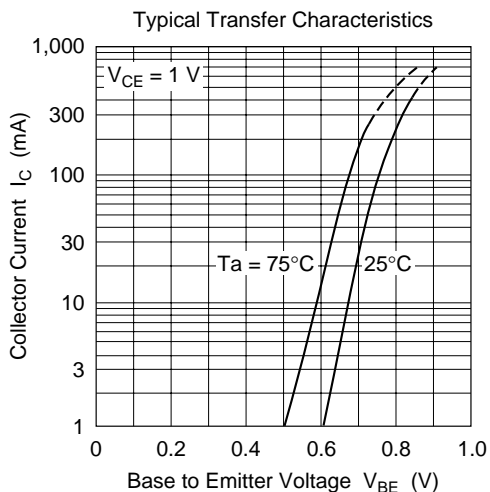
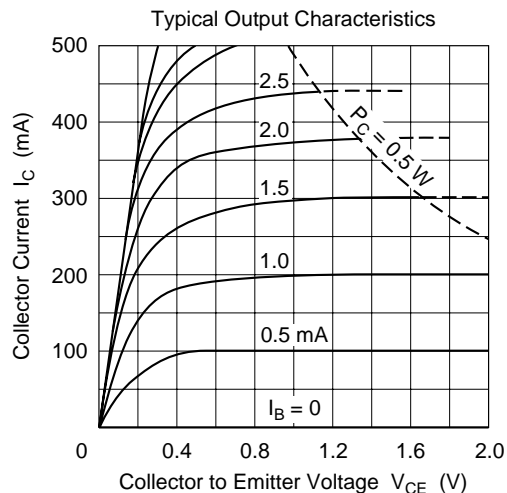
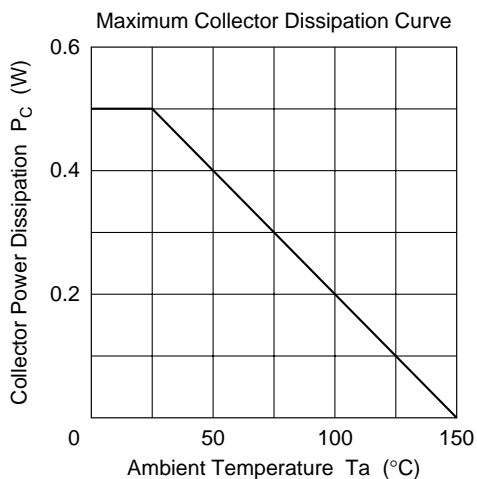
| Item | Symbol | Ratings | Unit |
|------------------------------|---------------|-------------|------|
| Collector to base voltage | V_{CBO} | 25 | V |
| Collector to emitter voltage | V_{CEO} | 20 | V |
| Emitter to base voltage | V_{EBO} | 5 | V |
| Collector current | I_C | 0.7 | A |
| Collector peak current | $i_{C(peak)}$ | 1.0 | A |
| Collector power dissipation | P_C | 0.5 | W |
| Junction temperature | T_j | 150 | °C |
| Storage temperature | T_{stg} | -55 to +150 | °C |

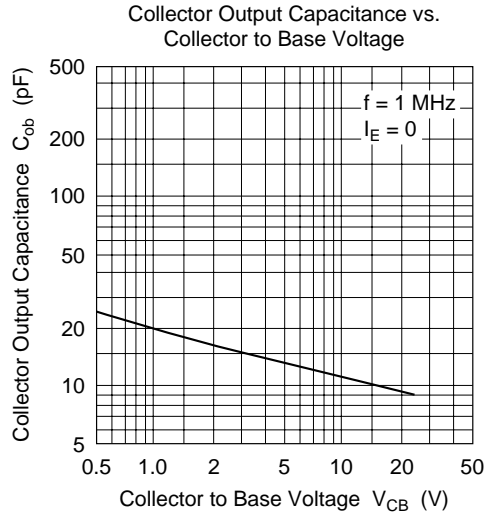
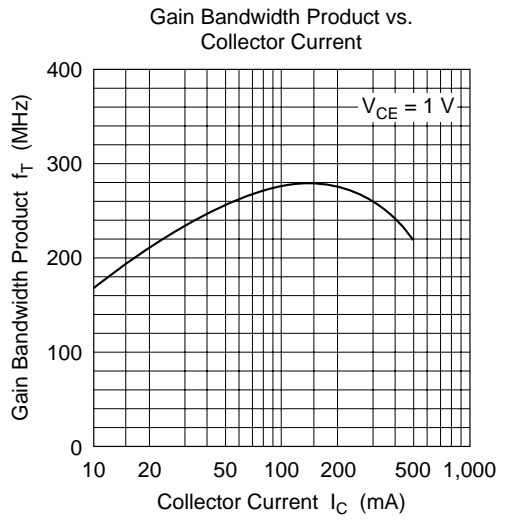
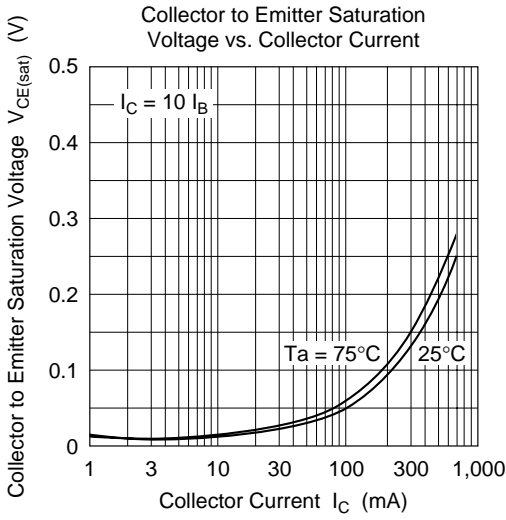
Electrical Characteristics (Ta = 25°C)

| Item | Symbol | Min | Typ | Max | Unit | Test conditions |
|---|---------------|-----|------|-----|---------|--|
| Collector to base breakdown voltage | $V_{(BR)CBO}$ | 25 | — | — | V | $I_C = 10 \mu A, I_E = 0$ |
| Collector to emitter breakdown voltage | $V_{(BR)CEO}$ | 20 | — | — | V | $I_C = 1 \text{ mA}, R_{BE} = \infty$ |
| Emitter to base breakdown voltage | $V_{(BR)EBO}$ | 5 | — | — | V | $I_E = 10 \mu A, I_C = 0$ |
| Collector cutoff current | I_{CBO} | — | — | 1.0 | μA | $V_{CB} = 20 \text{ V}, I_E = 0$ |
| DC current transfer ratio | h_{FE}^{*1} | 85 | — | 240 | | $V_{CE} = 1 \text{ V}, I_C = 0.15 \text{ A}$ (Pulse test) |
| Collector to emitter saturation voltage | $V_{CE(sat)}$ | — | 0.19 | 0.5 | V | $I_C = 0.5 \text{ A}, I_B = 0.05 \text{ A}$ (Pulse test) |
| Base to emitter voltage | V_{BE} | — | 0.76 | 1.0 | V | $V_{CE} = 1 \text{ V}, I_C = 0.15 \text{ A}$ (Pulse test) |
| Gain bandwidth product | f_T | — | 280 | — | MHz | $V_{CE} = 1 \text{ V}, I_C = 0.15 \text{ A}$ (Pulse test) |
| Collector output capacitance | C_{ob} | — | 12 | — | pF | $V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$ |

Note: 1. The 2SD467 is grouped by h_{FE} as follows.

| B | C |
|-----------|------------|
| 85 to 170 | 120 to 240 |

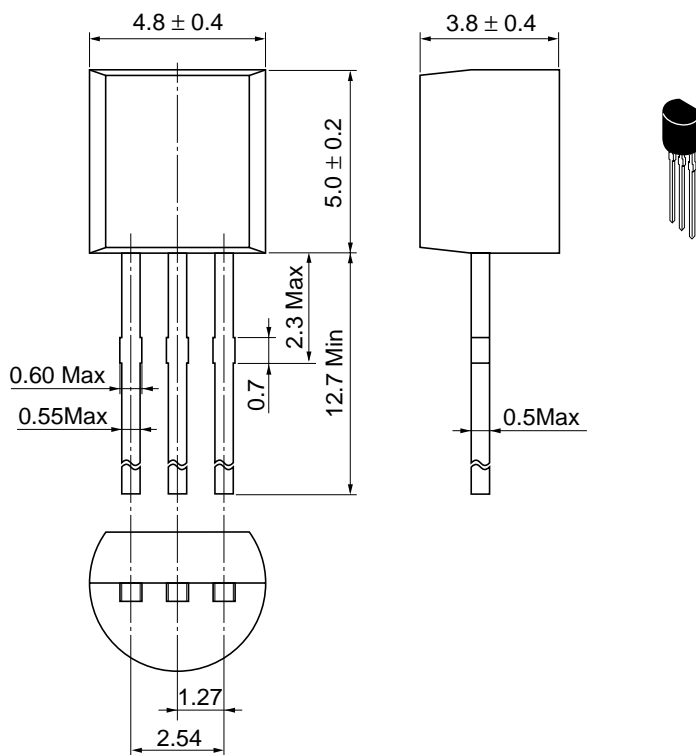




Package Dimensions

As of January, 2001

Unit: mm



| | |
|------------------------|-----------|
| Hitachi Code | TO-92 (1) |
| JEDEC | Conforms |
| EIAJ | Conforms |
| Mass (reference value) | 0.25 g |

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HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits.

Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL NorthAmerica : <http://semiconductor.hitachi.com/>
 Europe : <http://www.hitachi-eu.com/hel/ecg>
 Asia : <http://sicapac.hitachi-asia.com>
 Japan : <http://www.hitachi.co.jp/Sicd/indx.htm>

For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose, CA 95134
Tel: <1> (408) 433-1990
Fax: <1> (408) 433-0223

Hitachi Europe GmbH
Electronic Components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 585160

Hitachi Asia Ltd.
Hitachi Tower
16 Collyer Quay #20-00,
Singapore 049318
Tel : <65>-538-6533/538-8577
Fax : <65>-538-6933/538-3877
URL : <http://www.hitachi.com.sg>

Hitachi Asia Ltd.
(Taipei Branch Office)
4/F, No. 167, Tun Hwa North Road,
Hung-Kuo Building,
Taipei (105), Taiwan
Tel : <886>-(2)-2718-3666
Fax : <886>-(2)-2718-8180
Telex : 23222 HAS-TP
URL : <http://www.hitachi.com.tw>

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon,
Hong Kong
Tel : <852>-(2)-735-9218
Fax : <852>-(2)-730-0281
URL : <http://www.hitachi.com.hk>

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